

Application Data Sheet**Application Information**

Application Type::	National Phase
Subject Matter::	Utility
CD-ROM or CD-R:	None
Title::	METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL AND SILICON WAFER
Attorney Docket Number::	121356
Total Drawing Sheets::	3
Small Entity::	No

Applicant Information

Applicant Authority type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Izumi
Family Name::	FUSEGAWA
City of Residence::	Fukushima
Country of Residence::	Japan

Applicant Authority type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Sadayuki
Family Name::	OKUNI
City of Residence::	Fukushima
Country of Residence::	Japan

Applicant Authority type::	Inventor
Primary Citizenship Country::	Japan
Status::	Full Capacity
Given Name::	Nobuaki
Family Name::	MITAMURA

City of Residence:: Fukushima
Country of Residence:: Japan

Applicant Authority type:: Inventor
Primary Citizenship Country:: Japan
Status:: Full Capacity
Given Name:: Tomohiko
Family Name:: OHTA
City of Residence:: Fukushima
Country of Residence:: Japan

Applicant Authority type:: Inventor
Primary Citizenship Country:: Japan
Status:: Full Capacity
Given Name:: Nobuo
Family Name:: KATUOKA
City of Residence:: Fukushima
Country of Residence:: Japan

Correspondence Information

Correspondence Customer Number:: 25944

Domestic Priority Information			
Application::	Continuity Type::	Parent Application::	Parent Filing Date::
This Application is a	National Stage of	PCT/JP03/05167	04/23/03
Foreign Priority Information			
Country::	Application Number::	Filing Date::	Priority Claimed::
Japan	2002-122250	04/24/02	Yes
Assignee Information			
Assignee Name::		SHIN-ETSU HANDOTAI CO., LTD.	
Street of mailing address::		4-2, Marunouchi 1-chome, Chiyoda-ku	
City of mailing address::		Tokyo	
Country of mailing address::		Japan	
Postal or Zip Code of mailing address::		100-0005	